



STP40NF10L

N-CHANNEL 100V - 0.028Ω - 40A TO-220 LOW GATE CHARGE STripFET™ POWER MOSFET

| TYPE | V _{DSS} | R _{DS(on)} | I _D |
|------------|------------------|---------------------|----------------|
| STP40NF10L | 100 V | < 0.033 Ω | 40 A |

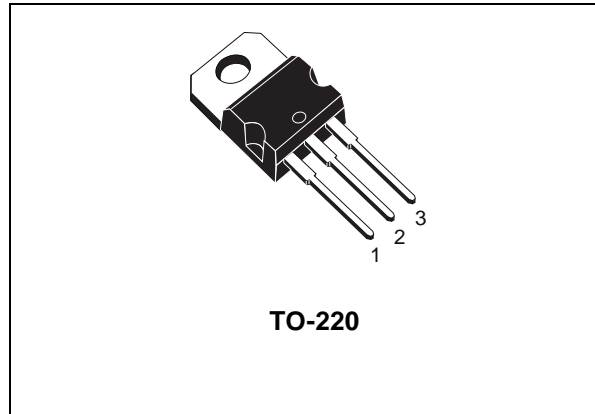
- TYPICAL R_{DS(on)} = 0.028Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION

DESCRIPTION

This Power Mosfet series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency isolated DC-DC converters for Telecom and Computer application. It is also intended for any application with low gate charge drive requirements.

APPLICATIONS

- HIGH-EFFICIENCY DC-DC CONVERTERS
- UPS AND MOTOR CONTROL
- AUTOMOTIVE



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|---------------------|--|------------|------|
| V _{DS} | Drain-source Voltage (V _{GS} = 0) | 100 | V |
| V _{DGR} | Drain-gate Voltage (R _{GS} = 20 kΩ) | 100 | V |
| V _{GS} | Gate- source Voltage | ± 15 | V |
| I _D | Drain Current (continuous) at T _C = 25°C | 40 | A |
| I _D | Drain Current (continuous) at T _C = 100°C | 25 | A |
| I _{DM} (●) | Drain Current (pulsed) | 160 | A |
| P _{TOT} | Total Dissipation at T _C = 25°C | 150 | W |
| | Derating Factor | 1 | W/°C |
| E _{AS} (1) | Single Pulse Avalanche Energy | 430 | mJ |
| T _{stg} | Storage Temperature | -65 to 175 | °C |
| T _j | Max. Operating Junction Temperature | 175 | °C |

(●) Pulse width limited by safe operating area

(1) Starting T_j = 25°C, I_D = 20A, V_{DD} = 40V

STP40NF10L

THERMAL DATA

| | | | |
|----------------|--|------|------|
| Rthj-case | Thermal Resistance Junction-case Max | 1 | °C/W |
| Rthj-amb | Thermal Resistance Junction-ambient Max | 62.5 | °C/W |
| T _l | Maximum Lead Temperature For Soldering Purpose | 300 | °C |

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------------|---|---|------|------|---------|----------|
| V _{(BR)DSS} | Drain-source Breakdown Voltage | I _D = 250 μA, V _{GS} = 0 | 100 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current (V _{GS} = 0) | V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C | | | 1 10 | μA μA |
| I _{GSS} | Gate-body Leakage Current (V _{DS} = 0) | V _{GS} = ± 15V | | | ±100 | nA |

ON (1)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|-----------------------------------|---|------|----------------|----------------|--------|
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = 250μA | 1 | 1.7 | 2.5 | V |
| R _{DS(on)} | Static Drain-source On Resistance | V _{GS} = 10V, I _D = 20 A V _{GS} = 5V, I _D = 20 A | | 0.028 0.030 | 0.033 0.036 | Ω Ω |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|------------------------------|---|------|------|------|------|
| g _{fs} (1) | Forward Transconductance | V _{DS} = 15V, I _D = 20 A | | 25 | | S |
| C _{iss} | Input Capacitance | V _{DS} = 25V, f = 1 MHz, V _{GS} = 0 | | 2300 | | pF |
| C _{oss} | Output Capacitance | | | 290 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 125 | | pF |

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------|--------------------|--|------|------|------|------|
| $t_{d(on)}$ | Turn-on Delay Time | $V_{DD} = 50\text{ V}, I_D = 20\text{ A}$ | | 25 | | ns |
| t_r | Rise Time | $R_G = 4.7\Omega, V_{GS} = 4.5\text{ V}$ (see test circuit, Figure 3) | | 82 | | ns |
| Q_g | Total Gate Charge | $V_{DD} = 80\text{ V}, I_D = 40\text{ A}, V_{GS} = 5\text{ V}$ | | 46 | 64 | nC |
| Q_{gs} | Gate-Source Charge | | | 12 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 22 | | nC |

SWITCHING OFF

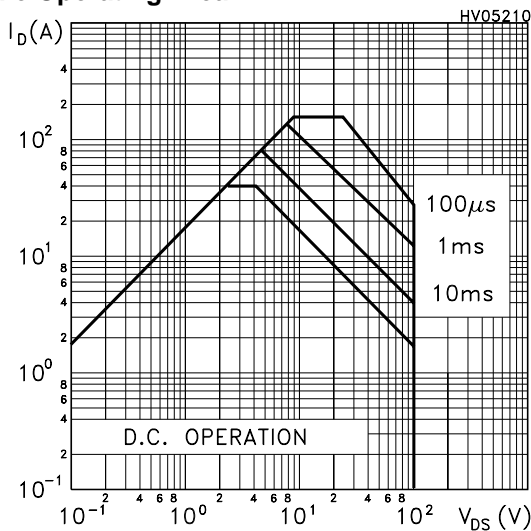
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------|-----------------------|--|------|------|------|------|
| $t_{d(off)}$ | Turn-off-Delay Time | $V_{DD} = 50\text{ V}, I_D = 20\text{ A},$ | | 64 | | ns |
| t_f | Fall Time | $R_G = 4.7\Omega, V_{GS} = 4.5\text{ V}$ (see test circuit, Figure 3) | | 24 | | ns |
| $t_{d(off)}$ | Off-voltage Rise Time | $V_{clamp} = 80\text{ V}, I_D = 40\text{ A}$ | | 51 | | ns |
| t_f | Fall Time | $R_G = 4.7\Omega, V_{GS} = 4.5\text{ V}$ | | 29 | | ns |
| t_c | Cross-over Time | (see test circuit, Figure 3) | | 53 | | ns |

SOURCE DRAIN DIODE

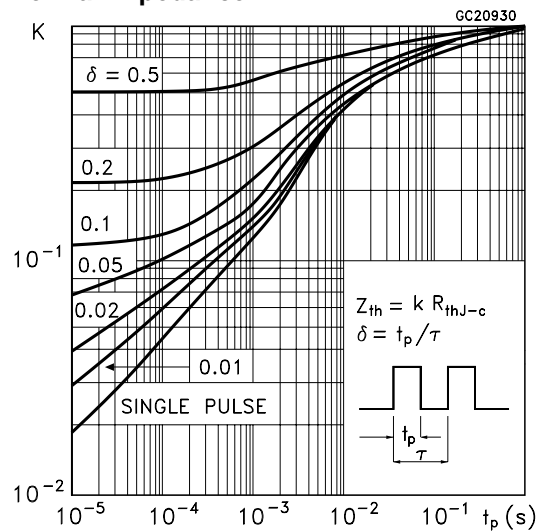
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------|-------------------------------|---|------|------|------|------|
| I_{SD} | Source-drain Current | | | | 40 | A |
| $I_{SDM(1)}$ | Source-drain Current (pulsed) | | | | 160 | A |
| $V_{SD(2)}$ | Forward On Voltage | $I_{SD} = 40\text{ A}, V_{GS} = 0$ | | | 1.3 | V |
| t_{rr} | Reverse Recovery Time | $I_{SD} = 40\text{ A}, di/dt = 100\text{ A}/\mu\text{s},$ | | 110 | | ns |
| Q_{rr} | Reverse Recovery Charge | $V_{DD} = 30\text{ V}, T_j = 150^\circ\text{C}$ | | 467 | | nC |
| I_{RRM} | Reverse Recovery Current | (see test circuit, Figure 5) | | 8 | | A |

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

Safe Operating Area

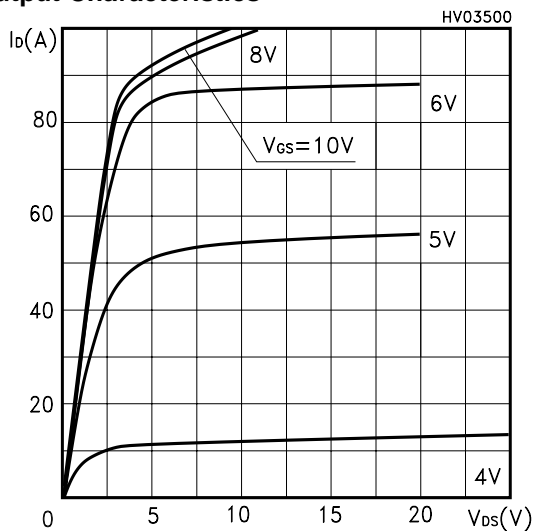


Thermal Impedance

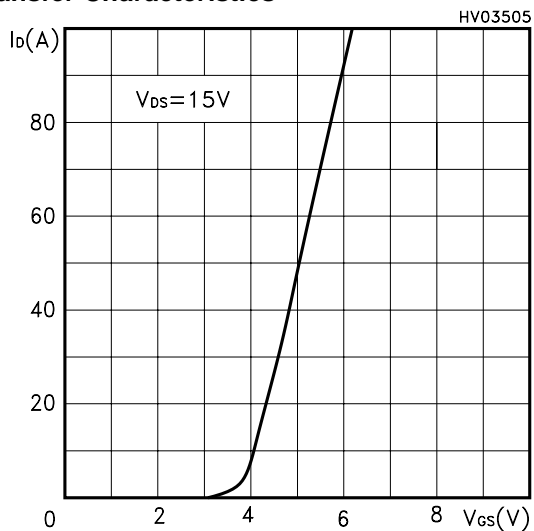


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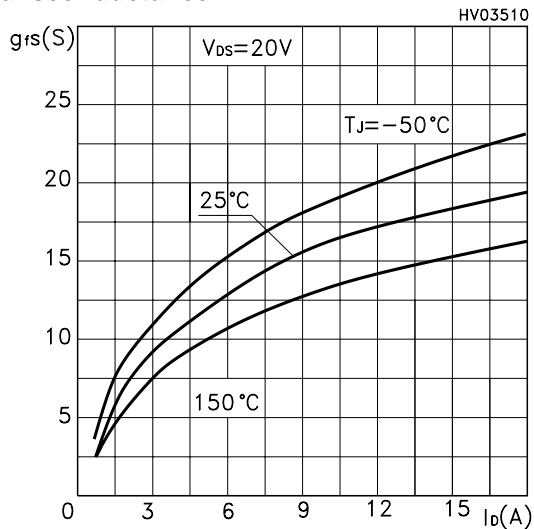
Output Characteristics



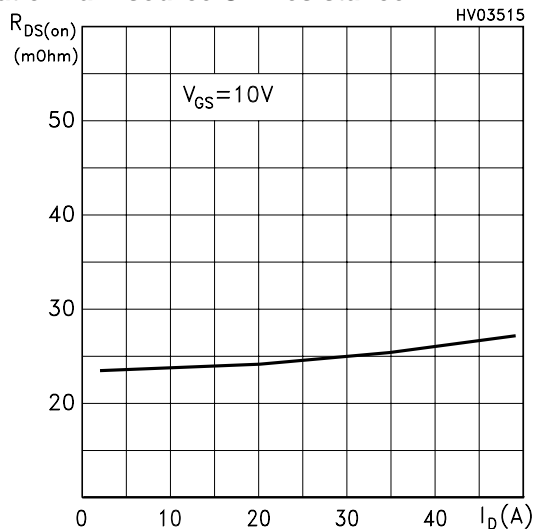
Transfer Characteristics



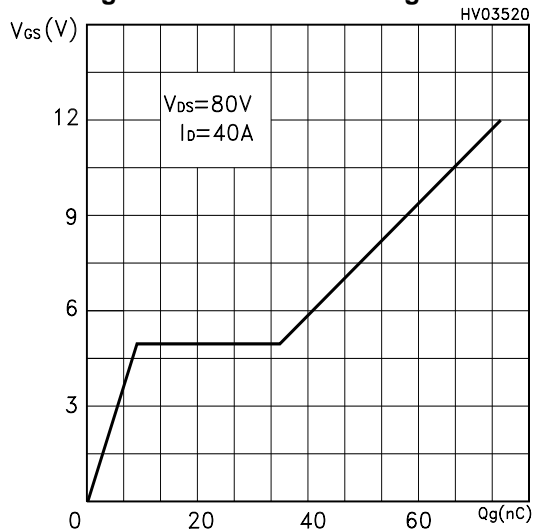
Transconductance



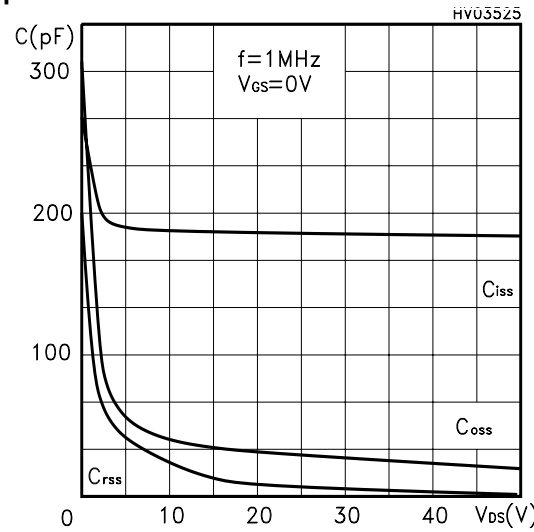
Static Drain-source On Resistance



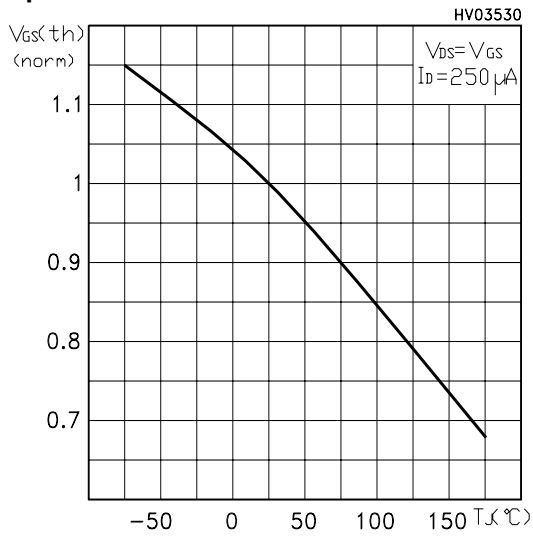
Gate Charge vs Gate-source Voltage



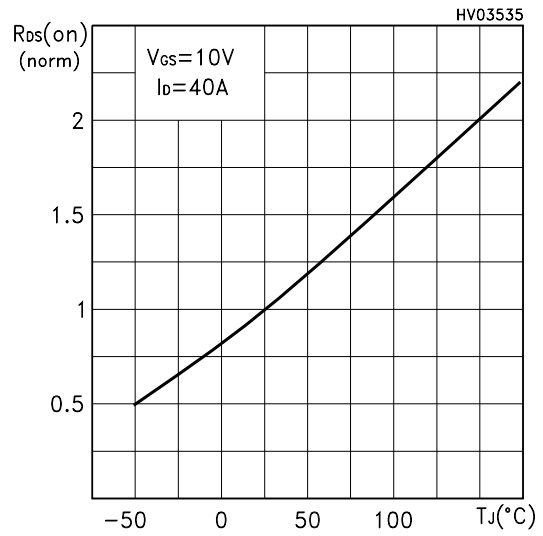
Capacitance Variations



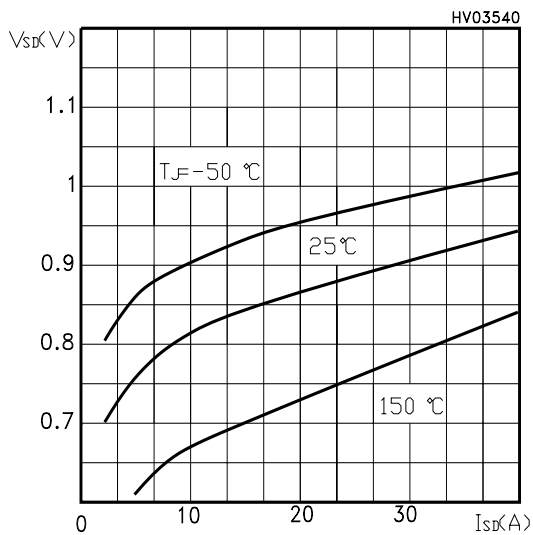
Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Drain-Source Breakdown vs Temperature

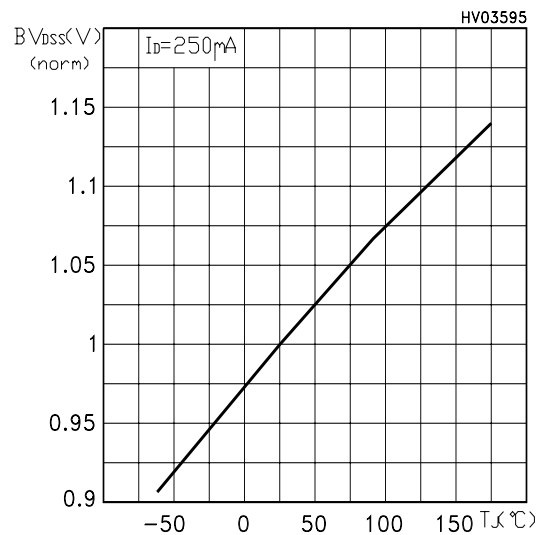


Fig. 1: Unclamped Inductive Load Test Circuit



Fig. 2: Unclamped Inductive Waveform



Fig. 3: Switching Times Test Circuit For Resistive Load



Fig. 4: Gate Charge test Circuit

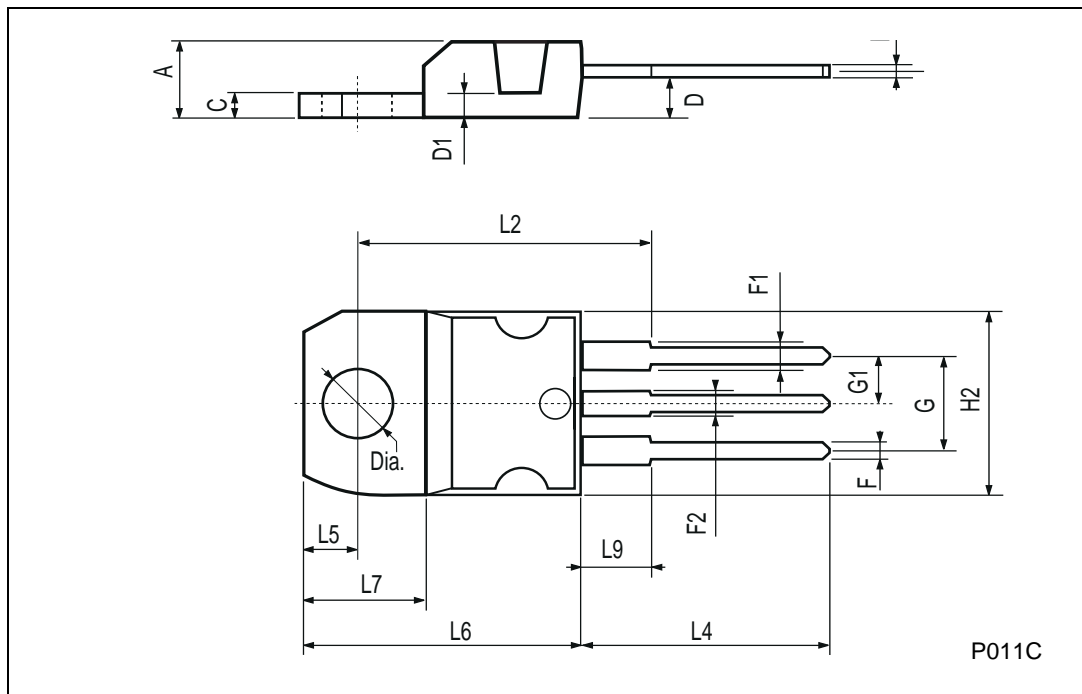


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-220 MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|-------|------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| C | 1.23 | | 1.32 | 0.048 | | 0.051 |
| D | 2.40 | | 2.72 | 0.094 | | 0.107 |
| D1 | | 1.27 | | | 0.050 | |
| E | 0.49 | | 0.70 | 0.019 | | 0.027 |
| F | 0.61 | | 0.88 | 0.024 | | 0.034 |
| F1 | 1.14 | | 1.70 | 0.044 | | 0.067 |
| F2 | 1.14 | | 1.70 | 0.044 | | 0.067 |
| G | 4.95 | | 5.15 | 0.194 | | 0.203 |
| G1 | 2.4 | | 2.7 | 0.094 | | 0.106 |
| H2 | 10.0 | | 10.40 | 0.393 | | 0.409 |
| L2 | | 16.4 | | | 0.645 | |
| L4 | 13.0 | | 14.0 | 0.511 | | 0.551 |
| L5 | 2.65 | | 2.95 | 0.104 | | 0.116 |
| L6 | 15.25 | | 15.75 | 0.600 | | 0.620 |
| L7 | 6.2 | | 6.6 | 0.244 | | 0.260 |
| L9 | 3.5 | | 3.93 | 0.137 | | 0.154 |
| DIA. | 3.75 | | 3.85 | 0.147 | | 0.151 |



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